



SEMI®
International
Standards

**INTERNATIONAL PV ANALYTICAL
TEST METHODS TASK FORCE**

Wednesday, March 23, 2011

10:00 – 12:30 PM

Berlin, Germany

- 1.0 Introductions
 - 1.1 Standards Membership Requirement
 - 1.2 Anti-trust Reminder
 - 1.3 Patentable Technologies Guidelines
 - 1.4 International Effective Meeting Guidelines
- 2.0 Agenda Review
- 3.0 Preliminary Ballot Review
 - 3.1 Doc. 5073, Revision of SEMI PV9-1110, Test Method for Excess Charge Carrier Decay in PV Silicon Materials by Non-Contact Measurements of Microwave Reflectance After a Short Illumination Pulse (*To be adjudicated at NA Spring Meeting, March 30*)
- 4.0 Old Business
 - 4.1 The plan for the Round Robin of SEMI PV9-1110 - Test Method for Excess Charge Carrier Decay in PV Silicon Materials by Non-Contact Measurements of Microwave Reflectance After a Short Illumination Pulse
 - 4.2 The plan for the Round Robin of SEMI PV10-1110 - Test Method for Instrumental Neutron Activation Analysis (INAA) of Silicon
- 5.0 New Business
 - 5.1 SNARF for Line Item Rev. of SEMI PV13-0211 - Test Method for Contactless Excess-Charge-Carrier Recombination Lifetime Measurement in Silicon Wafers, Ingots, and Bricks Using an Eddy-Current Sensor (Subj: “similar wafer” is not sufficiently precise”)
- 6.0 Next Task Force Meetings
 - 6.1 Tuesday, March 29 in San Jose, CA at NA Spring Standards Meetings
- 7.0 Action Item Review / Recommendations
- 8.0 Adjournment